





DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(TH)} <1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- ESD Protected Gate
- "Green" Device (Note 3)

Mechanical Data

• Case: SOT-563

 Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

• Terminal Connections: See Diagram

Terminals: Finish - Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208

Marking Information: See Page 3

• Ordering Information: See Page 3

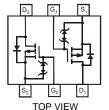
• Weight: 0.006 grams (approximate)

SOT-563









Internal Schematic

TOP VIEW

BOTTOM VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±8	V
Continuous Drain Current (Note 1) V _{GS} = -4.5V	I _D	-530	mA
Pulsed Drain Current	I _{DM}	-1.8	А

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _D	400	mW
Thermal Resistance, Junction to Ambient, Note 1	$R_{ heta JA}$	312.5	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-65 to +150	°C

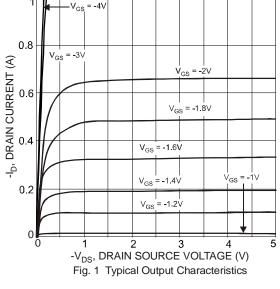
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20		_	V	$V_{GS} = 0V, I_D = -250mA$	
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)	ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.5		-1.0	٧	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			0.7	0.9		$V_{GS} = -4.5V$, $I_D = -430mA$	
Static Drain-Source On-Resistance	R _{DS} (ON)	_	1.1	1.4	Ω	$V_{GS} = -2.5V$, $I_D = -300mA$	
			1.7	2.0		$V_{GS} = -1.8V, I_D = -150mA$	
Forward Transfer Admittance	Y _{fs}	200	_	_	mS	$V_{DS} = -10V, I_{D} = -0.2A$	
Diode Forward Voltage (Note 4)	V_{SD}	-0.5	_	-1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss		_	175	pF	101/11/	
Output Capacitance	Coss			30	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		_	20	pF	1 - 1.0WH12	

Notes:

- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 4. Short duration pulse test used to minimize self-heating effect.





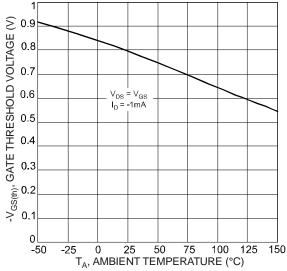
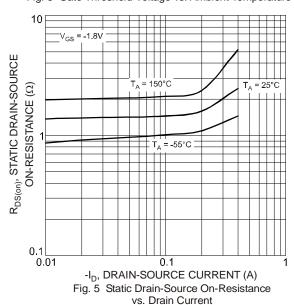


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature



1.0

V_{DS} = 5V

T_A = 150°C

T_A = 55°C

T_A = 25°C

T_A = 25°C

1.5

V_{DS} = 5V

T_A = 25°C

T_A = 25°C

T_A = 25°C

T_B = 25°C

T_A = 25°C

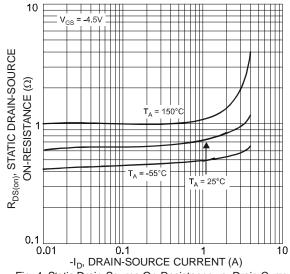


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

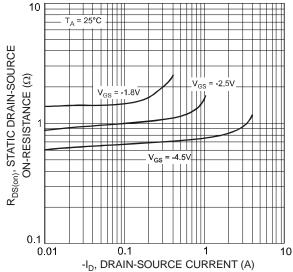


Fig. 6 Static Drain-Source On-Resistance vs.
Drain-Source Current



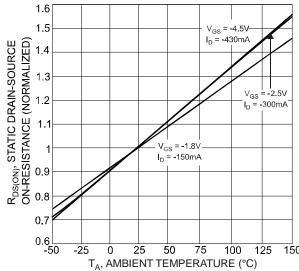


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

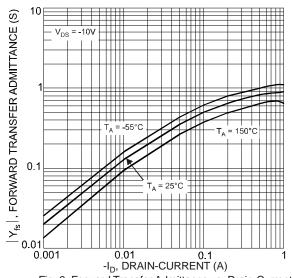


Fig. 9 Forward Transfer Admittance vs. Drain-Current

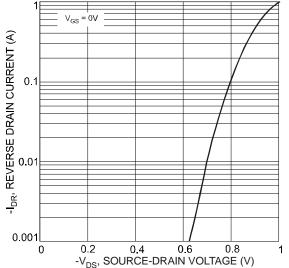
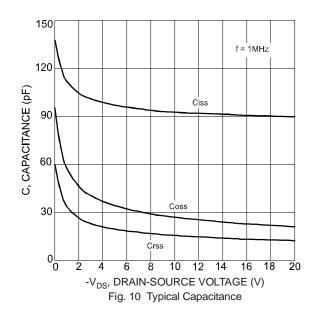


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

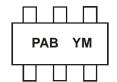


Ordering Information (Note 5)

Ī	Part Number	Case	Packaging
	DMP2004VK-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



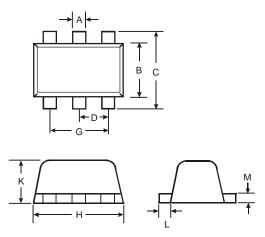
PAB = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	20	2007 2008		2009 2010		2011		2012				
Code	l	J	\	V W		X		Y		Z		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

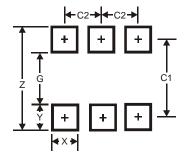


Package Outline Dimensions



SOT-563					
Dim	Min	Max	Тур		
Α	0.15	0.30	0.20		
В	1.10	1.25	1.20		
С	1.55	1.70	1.60		
D	-	-	0.50		
G	0.90	1.10	1.00		
Н	1.50	1.70	1.60		
K	0.55	0.60	0.60		
L	0.10	0.30	0.20		
M	0.10	0.18	0.11		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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